

Title (en)

ENHANCED STRUCTURE AND METHOD FOR BURIED LOCAL INTERCONNECTS

Title (de)

ERWEITERTE STRUKTUR UND VERFAHREN FÜR VERGRABENE LOKALE VERBINDUNGEN

Title (fr)

STRUCTURE ET PROCEDE AMELIORES POUR FORMER DES INTERCONNEXIONS LOCALES ENTERREES

Publication

**EP 1535341 A1 20050601 (EN)**

Application

**EP 02734808 A 20020614**

Priority

US 0219238 W 20020614

Abstract (en)

[origin: WO03107430A1] A structure and method is disclosed for forming a buried interconnect (10) of an integrated circuit in a single crystal semiconductor layer (12) of a substrate. The buried interconnect is formed of a deposited conductor and has one or more vertical sidewalls (18) which contact a single crystal region of an electronic device (20) formed in the single crystal semiconductor layer.

IPC 1-7

**H01L 29/40**; **H01L 21/82**

IPC 8 full level

**H01L 29/41** (2006.01); **H01L 21/3205** (2006.01); **H01L 21/74** (2006.01); **H01L 21/76** (2006.01); **H01L 21/762** (2006.01); **H01L 21/768** (2006.01); **H01L 21/82** (2006.01); **H01L 21/8234** (2006.01); **H01L 21/84** (2006.01); **H01L 23/52** (2006.01); **H01L 23/535** (2006.01); **H01L 27/08** (2006.01); **H01L 27/088** (2006.01); **H01L 27/12** (2006.01); **H01L 29/40** (2006.01); **H01L 29/423** (2006.01); **H01L 29/786** (2006.01); **H01L 29/78** (2006.01)

CPC (source: EP KR)

**H01L 21/743** (2013.01 - EP); **H01L 21/76895** (2013.01 - EP); **H01L 21/84** (2013.01 - EP); **H01L 23/535** (2013.01 - EP); **H01L 27/1203** (2013.01 - EP); **H01L 29/40** (2013.01 - KR); **H01L 29/42384** (2013.01 - EP); **H01L 29/78612** (2013.01 - EP); **H01L 29/7839** (2013.01 - EP); **H01L 2924/0002** (2013.01 - EP)

Citation (search report)

See references of WO 03107430A1

Designated contracting state (EPC)

AT BE CH CY DE DK ES FI FR GB GR IE IT LI LU MC NL PT SE TR

DOCDB simple family (publication)

**WO 03107430 A1 20031224**; AU 2002306174 A1 20031231; CN 1628387 A 20050615; EP 1535341 A1 20050601; JP 2005530347 A 20051006; KR 20050014839 A 20050207

DOCDB simple family (application)

**US 0219238 W 20020614**; AU 2002306174 A 20020614; CN 02828989 A 20020614; EP 02734808 A 20020614; JP 2004514138 A 20020614; KR 20047019133 A 20020614